

# Luca Montesi

## List of Publications by Year in descending order

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Version: 2024-02-01

17  
papers

442  
citations

840119

11  
h-index

1199166

12  
g-index

17  
all docs

17  
docs citations

17  
times ranked

566  
citing authors

#	ARTICLE	IF	CITATIONS
1	Structural changes and conductance thresholds in metal-free intrinsic SiO <sub>x</sub> resistive random access memory. Journal of Applied Physics, 2015, 117, .	1.1	102
2	Intrinsic resistance switching in amorphous silicon oxide for high performance SiO <sub>x</sub> ReRAM devices. Microelectronic Engineering, 2017, 178, 98-103.	1.1	64
3	Conductance tomography of conductive filaments in intrinsic silicon-rich silica RRAM. Nanoscale, 2015, 7, 18030-18035.	2.8	62
4	Nanoscale Transformations in Metastable, Amorphous, Silicon-Rich Silica. Advanced Materials, 2016, 28, 7486-7493.	11.1	52
5	Intrinsic Resistance Switching in Amorphous Silicon Suboxides: The Role of Columnar Microstructure. Scientific Reports, 2017, 7, 9274.	1.6	41
6	Spike-Timing Dependent Plasticity in Unipolar Silicon Oxide RRAM Devices. Frontiers in Neuroscience, 2018, 12, 57.	1.4	24
7	Investigation of resistance switching in SiO <sub>x</sub> RRAM cells using a 3D multi-scale kinetic Monte Carlo simulator. Journal of Physics Condensed Matter, 2018, 30, 084005.	0.7	23
8	Microscopic and spectroscopic analysis of the nature of conductivity changes during resistive switching in silicon-rich silicon oxide. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 211-217.	0.8	21
9	Silica: Nanoscale Transformations in Metastable, Amorphous, Silicon-Rich Silica (Adv. Mater. 34/2016). Advanced Materials, 2016, 28, 7549-7549.	11.1	13
10	Nanosecond Analog Programming of Substoichiometric Silicon Oxide Resistive RAM. IEEE Nanotechnology Magazine, 2016, 15, 428-434.	1.1	13
11	High-Performance Resistance Switching Memory Devices Using Spin-On Silicon Oxide. IEEE Nanotechnology Magazine, 2018, 17, 884-888.	1.1	11
12	Conductive AFM Topography of Intrinsic Conductivity Variations in Silica Based Dielectrics for Memory Applications. ECS Transactions, 2016, 75, 3-9.	0.3	7
13	Advanced physical modeling of SiO <sub>x</sub> resistive random access memories. , 2016, , .		6
14	Building Blocks to Use in Innovative Non-volatile FPGA Architecture Based on MTJs. , 2012, , .		3
15	Resistance switching in SiO <sub>x</sub> . , 2015, , .		0
16	Structural investigation of resistance switching in silicon-rich silica films. , 2015, , .		0
17	Silicon Oxide Reram Device. ECS Meeting Abstracts, 2016, , .	0.0	0